MOSFETs Silicon N-channel MOS (U-MOSⅧ-H)

TPH8R903NL

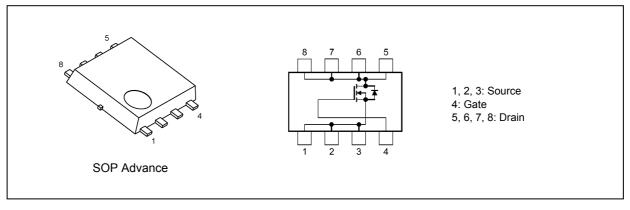
1. Applications

- Switching Voltage Regulators
- DC-DC Converters

2. Features

- (1) High-speed switching
- (2) Small gate charge: $Q_{SW} = 2.5 \text{ nC}$ (typ.)
- (3) Low drain-source on-resistance: $R_{DS(ON)} = 10.2 \text{ m}\Omega \text{ (typ.)} (V_{GS} = 4.5 \text{ V})$
- (4) Low leakage current: $I_{DSS} = 10 \ \mu A \ (max) \ (V_{DS} = 30 \ V)$
- (5) Enhancement mode: V_{th} = 1.3 to 2.3 V (V_{DS} = 10 V, I_D = 0.1 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25 \,^{\circ}C$ unless otherwise specified)

Characteris	Symbol	Rating	Unit		
Drain-source voltage			V _{DSS}	30	V
Gate-source voltage			V _{GSS}	±20]
Drain current (DC)	(Silicon limit)	(Note 1), (Note 2)	I _D	38	A
Drain current (DC)	(T _c = 25 °C)	(Note 1)	I _D	20]
Drain current (pulsed)	(t = 1 ms)	(Note 1)	I _{DP}	78	1
Power dissipation	(T _c = 25 °C)		PD	24	W
Power dissipation	(t = 10 s)	(Note 3)	PD	2.8]
Power dissipation	(t = 10 s)	(Note 4)	PD	1.6	1
Single-pulse avalanche energy		(Note 5)	E _{AS}	23	mJ
Avalanche current	·		I _{AR}	20	A
Channel temperature			T _{ch}	150	°C
Storage temperature	·		T _{stg}	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit		
Channel-to-case thermal resistance	(T _c = 25 °C)		R _{th(ch-c)}	5.2	°C/W
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 3)	R _{th(ch-a)}	44.6	
Channel-to-ambient thermal resistance	(t = 10 s)	(Note 4)	R _{th(ch-a)}	78.1	

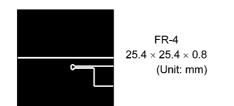
Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: Limited by silicon chip capability.

Note 3: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 4: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 5: V_{DD} = 24 V, T_{ch} = 25 °C (initial), L = 45 μ H, I_{AR} = 20 A



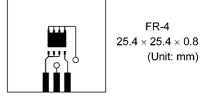


Fig. 5.1 Device Mounted on a Glass-Epoxy Board (a) Fig. 5.2 Device Mounted on a Glass-Epoxy Board (b)

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	_		±0.1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 30 V, V _{GS} = 0 V	_		10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	30		_	V
	V _{(BR)DSX}	I _D = 10 mA, V _{GS} = -20 V	15	_	_	
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 0.1 mA	1.3		2.3	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 4.5 V, I _D = 6 A	_	10.2	12.7	mΩ
		V _{GS} = 10 V, I _D = 10 A	_	7.6	8.9	

6.2. Dynamic Characteristics ($T_a = 25$ °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz		630	820	pF
Reverse transfer capacitance	C _{rss}		_	21	52	
Output capacitance	C _{oss}]		350	_	
Gate resistance	r _g	—	_	1.1	1.7	Ω
Switching time (rise time)	tr	See Fig. 6.2.1.	_	2.4	_	ns
Switching time (turn-on time)	t _{on}			8.3	_	
Switching time (fall time)	t _f]		2.1		
Switching time (turn-off time)	t _{off}]	_	14	_	

$$V_{GS} \stackrel{10}{}_{0}V \stackrel{1}{\underset{}}_{V} \stackrel{1}{\underset{}}{\underset{}}_{V} \stackrel{1}{\underset{}}_{V} \overset{1}{\underset{}}_{V} \overset{1}{\underset{}}_{V} \overset{}$$

Duty \leq 1%, t_w = 10 μ s

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25$ °C unless otherwise specified)

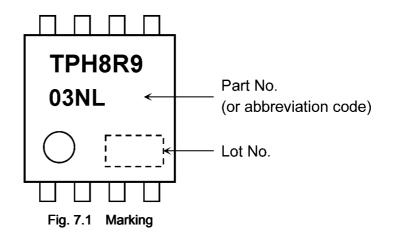
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus	Qg	$V_{DD} \approx 15 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	_	9.8	—	nC
gate-drain)		$V_{DD} \approx 15 \text{ V}, \text{ V}_{GS}$ = 4.5 V, I _D = 20 A	_	4.4	_	
Gate-source charge 1	Q _{gs1}	$V_{DD} \approx 15 \text{ V}, \text{ V}_{GS}$ = 10 V, I _D = 20 A	—	2.6	_	
Gate-drain charge	Q _{gd}		_	1.3	—	
Gate switch charge	Q _{SW}			2.5	_	

6.4. Source-Drain Characteristics ($T_a = 25 \ ^{\circ}C$ unless otherwise specified)

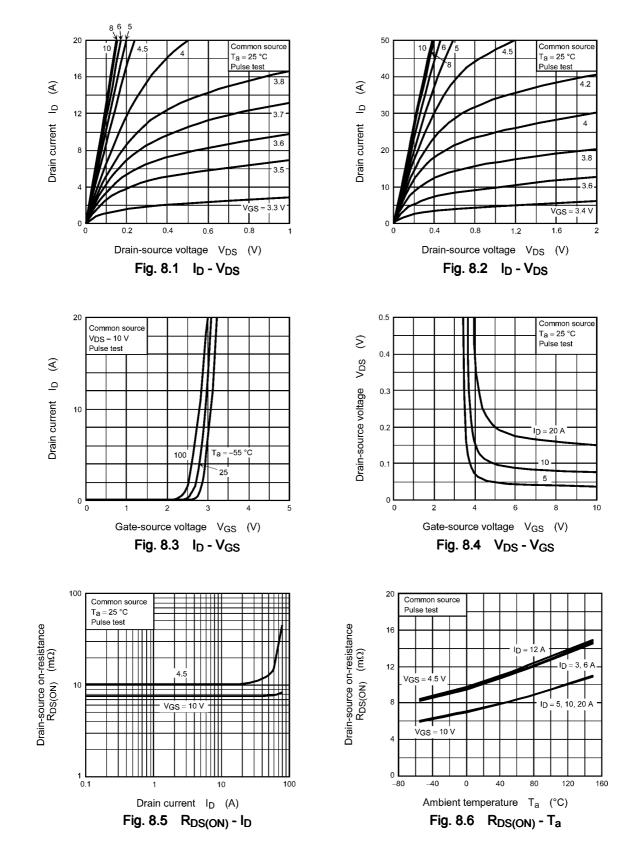
Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (pulsed)	(Note 6)	I _{DRP}	—	_	_	78	А
Diode forward voltage		V _{DSF}	I _{DR} = 20 A, V _{GS} = 0 V	_		-1.2	V

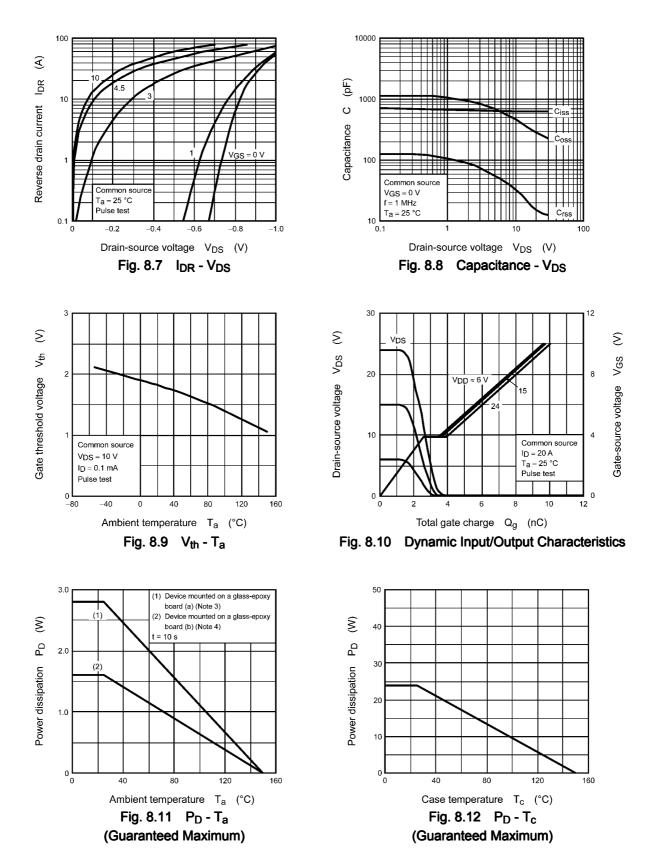
Note 6: Ensure that the channel temperature does not exceed 150 °C.

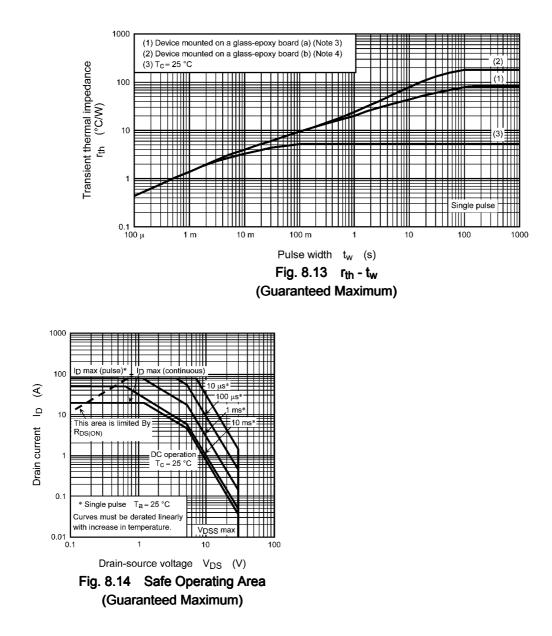
7. Marking



8. Characteristics Curves (Note)







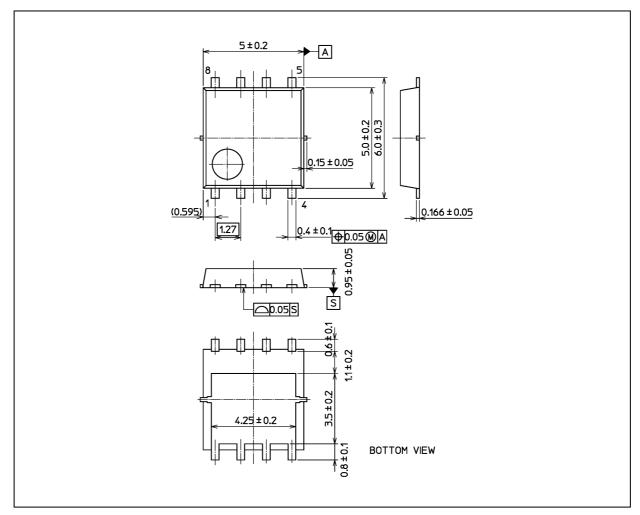
Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



TPH8R903NL

Package Dimensions

Unit: mm



Weight: 0.069 g (typ.)

TOSHIBA: 2-5Q1S

Nickname: SOP Advance

Package Name(s)

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